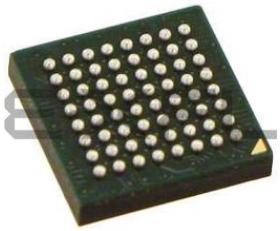

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Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, SPI, UART/USART, USB
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	50
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LFBGA
Supplier Device Package	64-MAPBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl27z256vmp4

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1.4 Voltage and current operating ratings

Table 4. Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	120	mA
V_{IO}	IO pin input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V
V_{USB_DP}	USB_DP input voltage	–0.3	3.63	V
V_{USB_DM}	USB_DM input voltage	–0.3	3.63	V
V_{REGIN}	USB regulator input	–0.3	6.0	V

2 General

2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

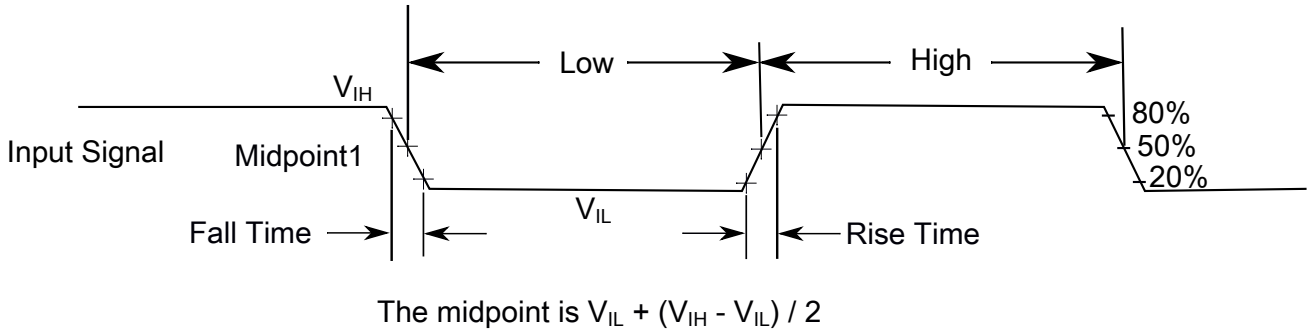


Figure 1. Input signal measurement reference

All digital I/O switching characteristics, unless otherwise specified, assume that the output pins have the following characteristics.

- C_L=30 pF loads
- Slew rate disabled
- Normal drive strength

2.2 Nonswitching electrical specifications

2.2.1 Voltage and current operating requirements

Table 5. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	–0.1	0.1	V	
$V_{SS} – V_{SSA}$	V_{SS}-to-V_{SSA} differential voltage	–0.1	0.1	V	
V_{IH}	Input high voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 0.7 × V_{DD} 0.75 × V_{DD}	 — —	 V V	
V_{IL}	Input low voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 — —	 0.35 × V_{DD} 0.3 × V_{DD}	 V V	
V_{HYS}	Input hysteresis	0.06 × V_{DD}	—	V	
I_{ICIO}	IO pin negative DC injection current — single pin • V_{IN} < V_{SS}-0.3V	-3	—	mA	1
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents of 16 contiguous pins • Negative current injection	-25	—	mA	
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	2
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	

1. All I/O pins are internally clamped to V_{SS} through a ESD protection diode. There is no diode connection to V_{DD}. If V_{IN} greater than V_{IO_MIN} (= V_{SS}-0.3 V) is observed, then there is no need to provide current limiting resistors at the pads. If this limit cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as R = (V_{IO_MIN} - V_{IN})/|I_{ICIO}|.
2. Open drain outputs must be pulled to V_{DD}.

2.2.2 LVD and POR operating requirements

Table 6. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling V_{DD} POR detect voltage	0.8	1.1	1.5	V	—

Table continues on the next page...

Table 8. Power mode transition operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• LLS → RUN	—	7.5	8	µs	
	• VLPS → RUN	—	7.5	8	µs	
	• STOP → RUN	—	7.5	8	µs	

1. Normal boot (FTFA_FOPT[LPBOOT]=11)

2.2.5 Power consumption operating behaviors

The maximum values stated in the following table represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).

NOTE

The while (1) test is executed with flash cache enabled.

Table 9. Power consumption operating behaviors

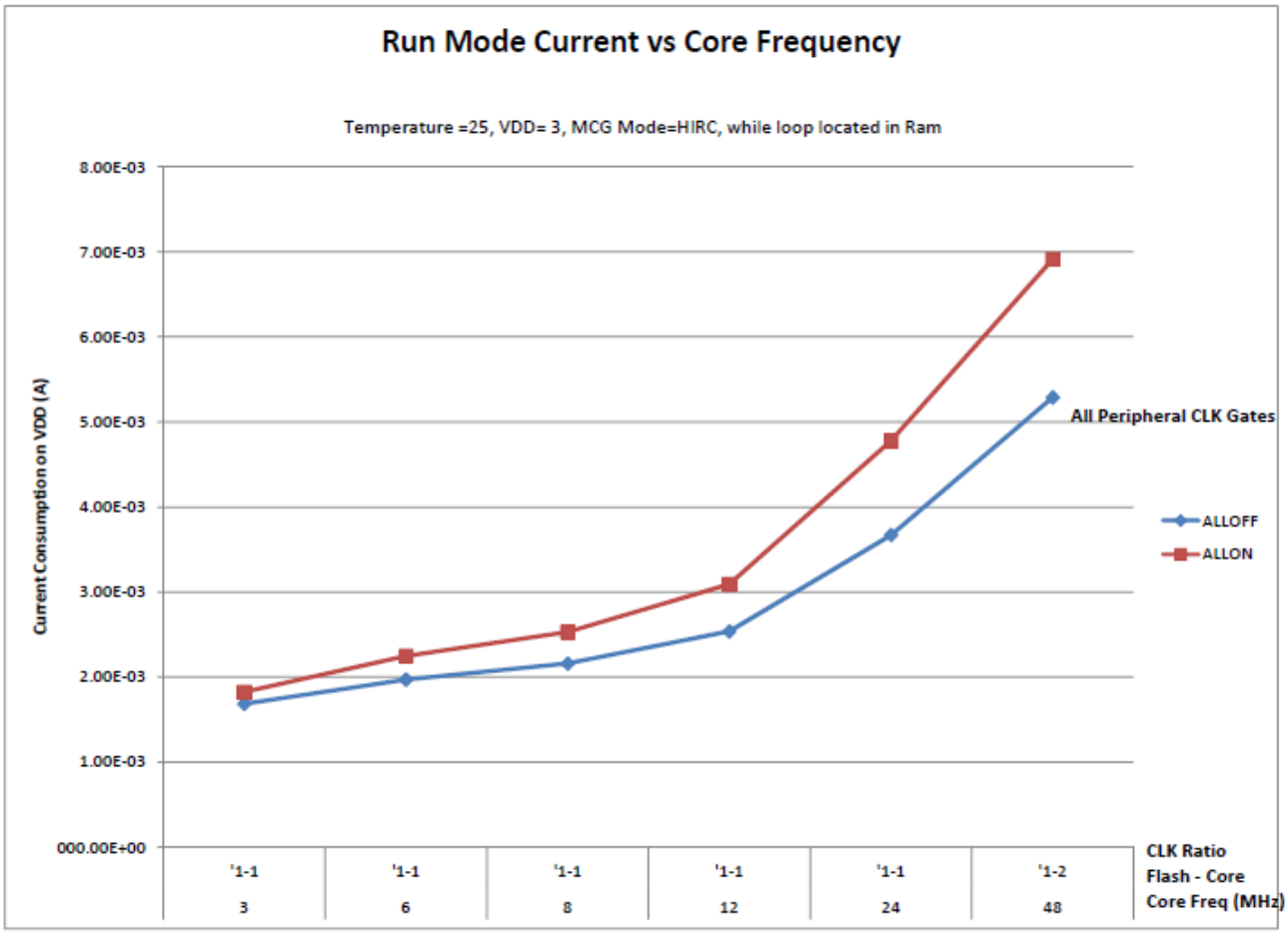
Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUNCO}	Running CoreMark in flash in compute operation mode—48M HIRC mode, 48 MHz core / 24 MHz flash, V_{DD} = 3.0 V					2
	• at 25 °C	—	5.76	6.40	mA	
	• at 105 °C	—	6.04	6.68		
I_{DD_RUNCO}	Running While(1) loop in flash in compute operation mode—48M HIRC mode, 48 MHz core / 24 MHz flash, V_{DD} = 3.0 V					
	• at 25 °C	—	3.21	3.85	mA	
	• at 105 °C	—	3.49	4.13		
I_{DD_RUN}	Run mode current—48M HIRC mode, running CoreMark in Flash all peripheral clock disable 48 MHz core/24 MHz flash, V_{DD} = 3.0 V					2
	• at 25 °C	—	6.45	7.09	mA	
	• at 105 °C	—	6.75	7.39		
I_{DD_RUN}	Run mode current—48M HIRC mode, running CoreMark in flash all peripheral clock disable, 24 MHz core/12 MHz flash, V_{DD} = 3.0 V					2
		—	3.95	4.59		
		—	4.23	4.87	mA	

Table continues on the next page...

Table 9. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• at 25 °C • at 105 °C					
I_{DD_VLPRCO}	Very Low Power Run Core Mark in Flash in Compute Operation mode: Core@4MHz, Flash @1MHz, V_{DD} = 3.0 V • at 25 °C	—	826	907	µA	
I_{DD_VLPRCO}	Very-low-power-run While(1) loop in SRAM in compute operation mode— 8 MHz LIRC mode, 4 MHz core / 1 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	405	486	µA	
I_{DD_VLPRCO}	Very-low-power run While(1) loop in SRAM in compute operation mode:—2 MHz LIRC mode, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	154	235	µA	
I_{DD_VLPR}	Very-low-power run mode current— 2 MHz LIRC mode, While(1) loop in flash all peripheral clock disable, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	108	189	µA	
I_{DD_VLPR}	Very-low-power run mode current— 2 MHz LIRC mode, While(1) loop in flash all peripheral clock disable, 125 kHz core / 31.25 kHz flash, V_{DD} = 3.0 V • at 25 °C	—	39	120	µA	
I_{DD_VLPR}	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in flash all peripheral clock disable, 4 MHz core / 1 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	249	330	µA	
I_{DD_VLPR}	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in flash all peripheral clock enable, 4 MHz core / 1 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	337	418	µA	
I_{DD_VLPR}	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in SRAM in all peripheral clock disable, 4 MHz core / 1 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	416	497	µA	
I_{DD_VLPR}	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in SRAM all peripheral clock enable, 4 MHz core / 1 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	494	575	µA	
I_{DD_VLPR}	Very-low-power run mode current—2 MHz LIRC mode, While(1) loop in SRAM in all peripheral clock disable, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	166	247	µA	
I_{DD_VLPR}	Very-low-power run mode current—2 MHz LIRC mode, While(1) loop in SRAM all peripheral clock					

Table continues on the next page...


Run Mode Current vs Core Frequency
Temperature =25, VDD= 3, MCG Mode=HIRC, while loop located in Ram
Current Consumption on VDD (A)
8.00E-03
7.00E-03
6.00E-03
5.00E-03
4.00E-03
3.00E-03
2.00E-03
1.00E-03
000.00E+00
All Peripheral CLK Gates
ALLOFF
ALLON
'1-1
3
'1-1
6
'1-1
8
'1-1
12
'1-1
24
'1-2
48
CLK Ratio
Flash - Core
Core Freq (MHz)

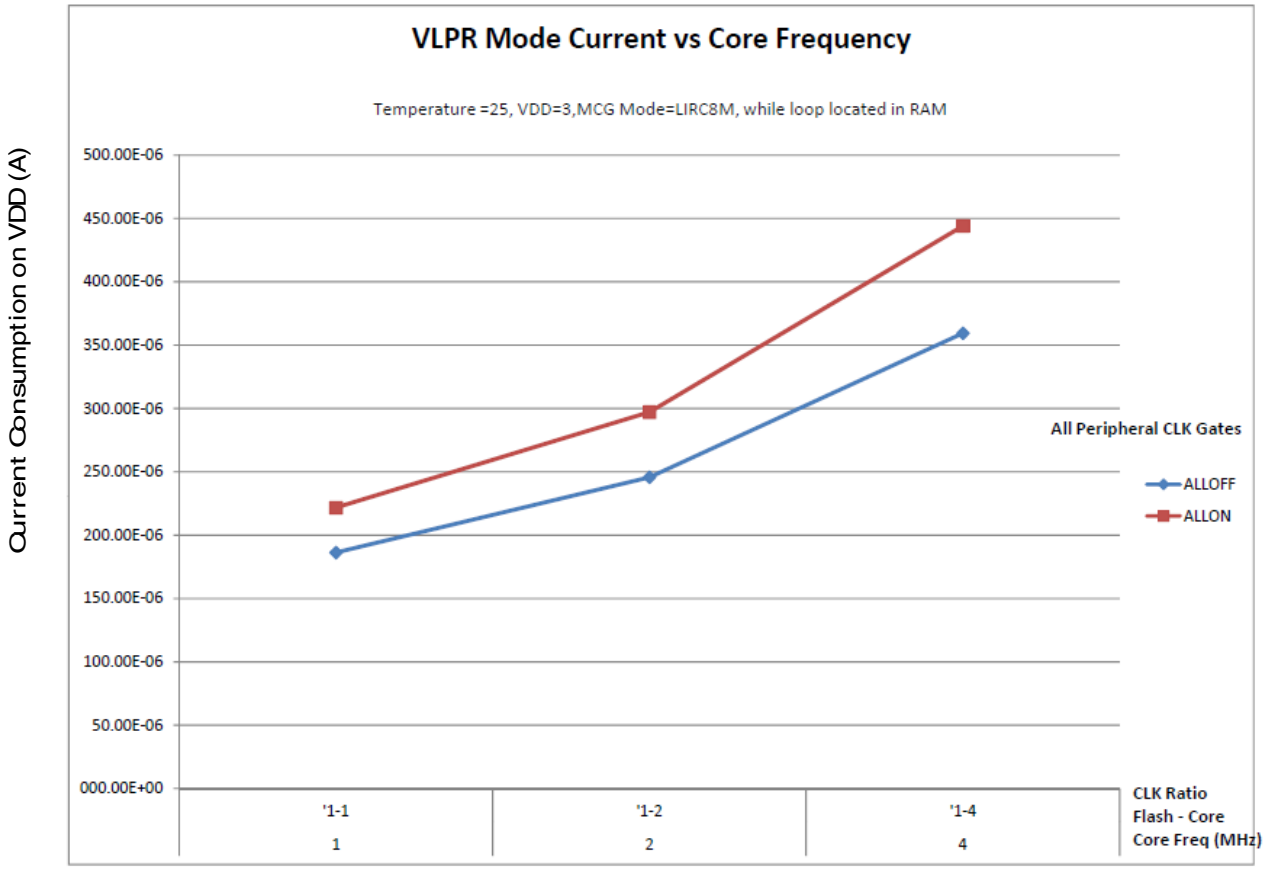


Figure 3. VLPR mode current vs. core frequency

2.2.6 EMC radiated emissions operating behaviors

Table 11. EMC radiated emissions operating behaviors for 64-pin LQFP package

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	11	dBµV	1, 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	12	dBµV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	10	dBµV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	6	dBµV	
V_{RE_IEC}	IEC level	0.15–1000	N	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement*

Table 13. Device clock specifications (continued)

Symbol	Description	Min.	Max.	Unit
f_{LPTMR}	LPTMR clock[3]	—	24	MHz
f_{LPTMR_ERCLK}	LPTMR external reference clock	—	16	MHz
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	—	16	MHz
f_{TPM}	TPM asynchronous clock	—	8	MHz
$f_{LPUART0/1}$	LPUART0/1 asynchronous clock	—	8	MHz

1. The maximum value of system clock, core clock, bus clock, and flash clock under normal run mode can be 3% higher than the specified maximum frequency when IRC 48MHz is used as the clock source.
2. The frequency limitations in VLPR and VLPS modes here override any frequency specification listed in the timing specification for any other module. These same frequency limits apply to VLPS, whether VLPS was entered from RUN or from VLPR.
3. The LPTMR can be clocked at this speed in VLPR or VLPS only when the source is an external pin.

2.3.2 General switching specifications

These general-purpose specifications apply to all signals configured for GPIO and UART signals.

Table 14. General switching specifications

Description	Min.	Max.	Unit	Notes
GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1
External RESET and NMI pin interrupt pulse width — Asynchronous path	100	—	ns	2
GPIO pin interrupt pulse width — Asynchronous path	16	—	ns	2
Port rise and fall time	—	36	ns	3

1. The synchronous and asynchronous timing must be met.
2. This is the shortest pulse that is guaranteed to be recognized.
3. 75 pF load

2.4 Thermal specifications

2.4.1 Thermal operating requirements

Table 15. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_J	Die junction temperature	–40	125	°C	
T_A	Ambient temperature	–40	105	°C	1

1. Maximum T_A can be exceeded only if the user ensures that T_J does not exceed the maximum. The simplest method to determine T_J is: $T_J = T_A + R_{\theta JA} \times$ chip power dissipation.

2.4.2 Thermal attributes

Table 16. Thermal attributes

Board type	Symbol	Description	48 QFN	32 QFN	64 LQFP	64 MAPBGA	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	86	101	70	50.3	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	29	33	51	42.9	°C/W	
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	71	84	58	41.4	°C/W	
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	24	28	45	38.0	°C/W	
—	$R_{\theta JB}$	Thermal resistance, junction to board	12	13	33	39.6	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	1.7	1.7	20	27.3	°C/W	3
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	2	3	4	0.4	°C/W	4
—	Ψ_{JB}	Thermal characterization parameter, junction to package bottom (natural convection)	-	-	-	12.6	°C/W	5

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*.
3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.

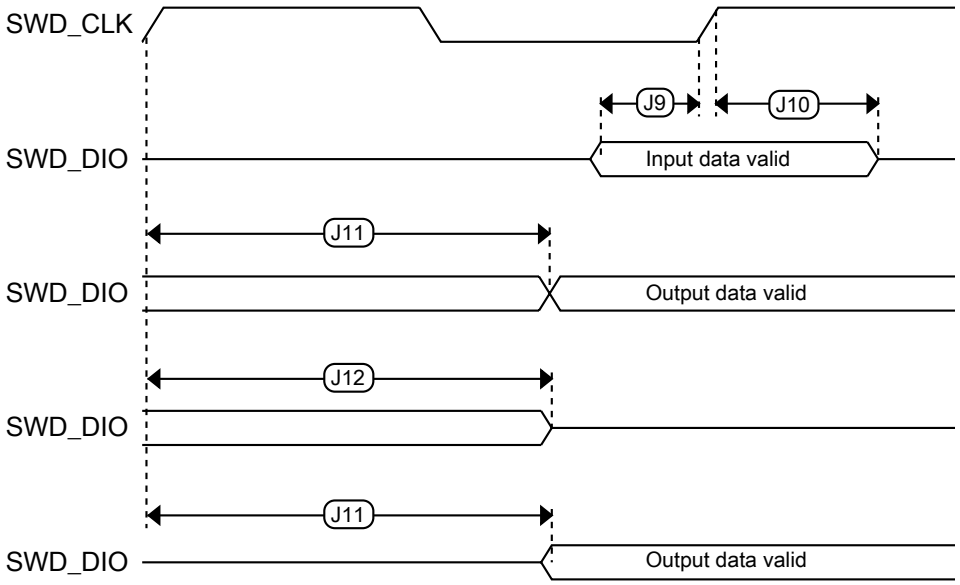


Figure 5. Serial wire data timing

3.2 System modules

There are no specifications necessary for the device's system modules.

3.3 Clock modules

3.3.1 MCG-Lite specifications

Table 18. IRC48M specification

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD}	Supply current	—	400	500	µA	—
f_{IRC}	Output frequency	—	48	—	MHz	—
$\Delta f_{irc48m\_ol\_lv}$	Open loop total deviation of IRC48M frequency at low voltage (VDD=1.71V-1.89V) over temperature	—	± 0.5	± 1.5	$\%f_{irc48m}$	1
$\Delta f_{irc48m\_ol\_hv}$	Open loop total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over temperature	—	± 0.5	± 1.0	$\%f_{irc48m}$	1

Table continues on the next page...

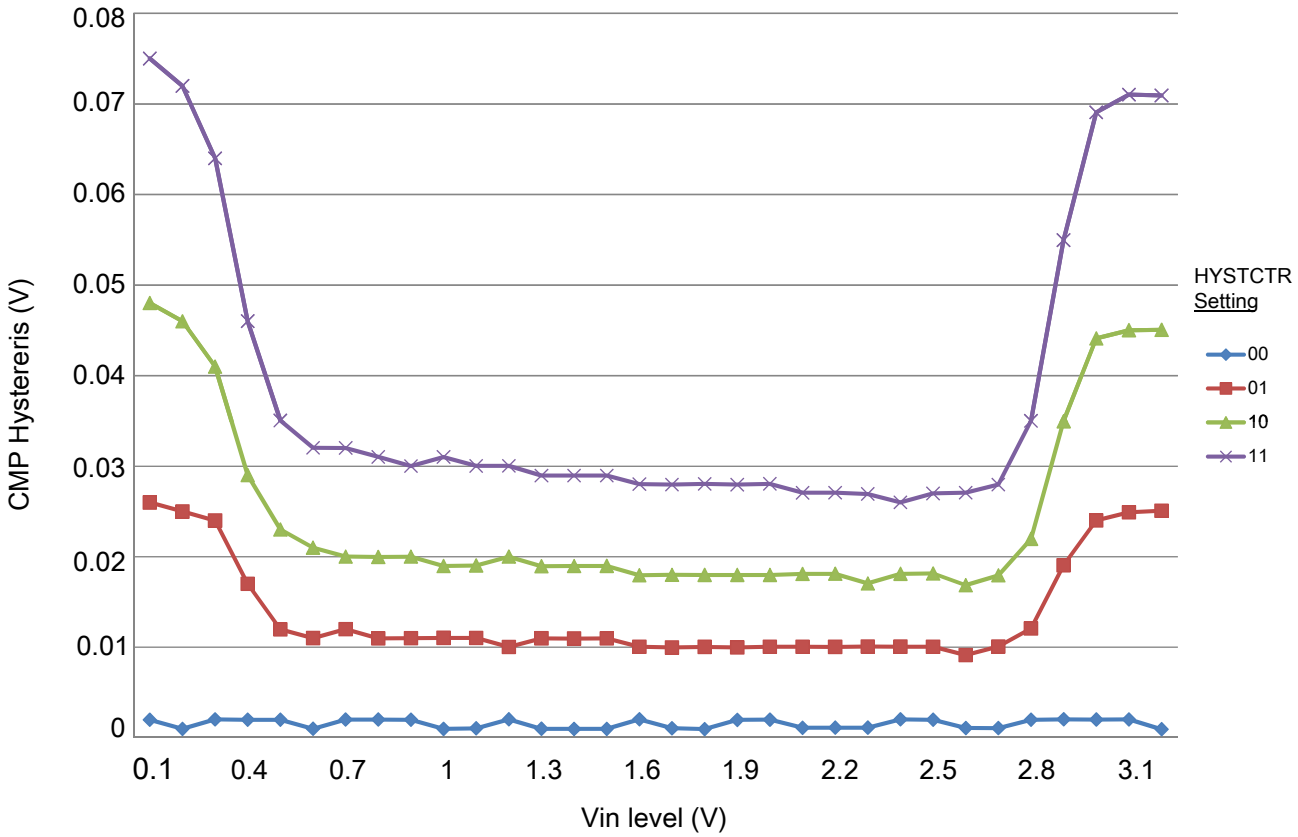


Figure 10. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

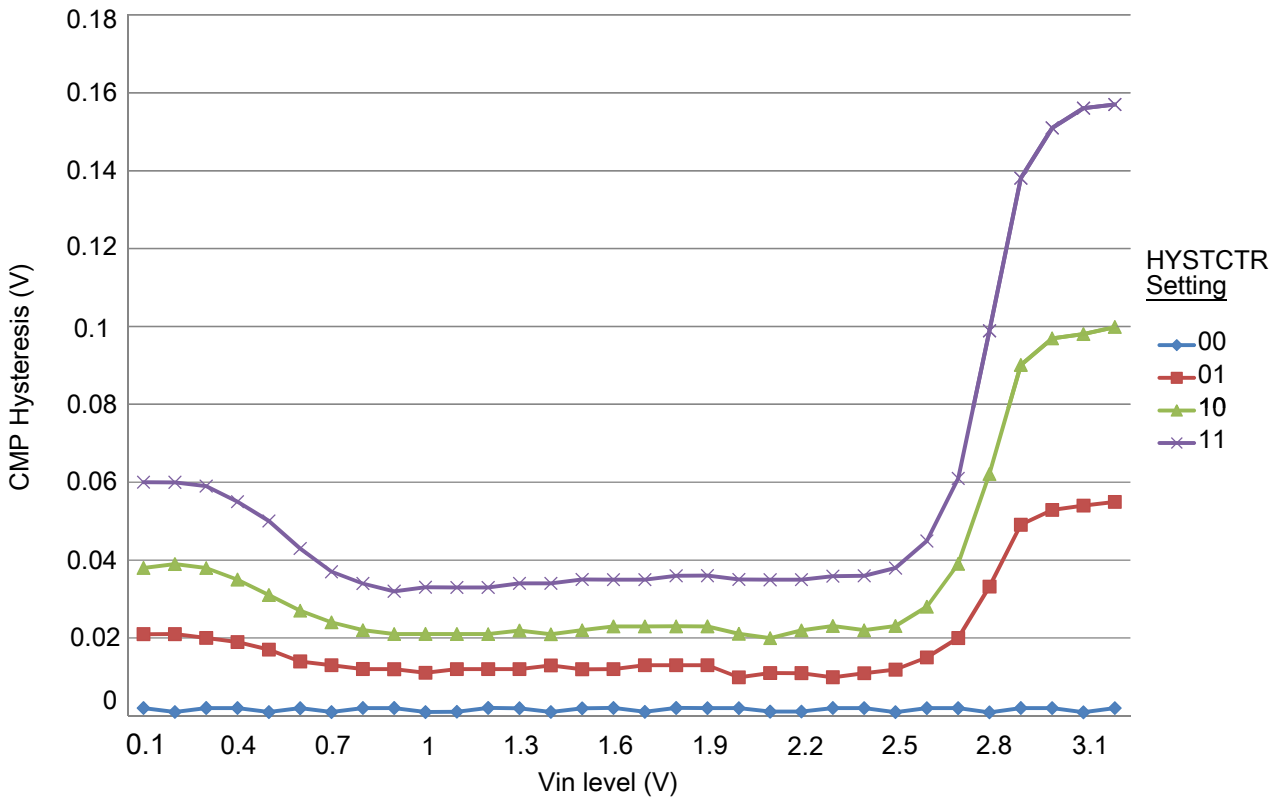


Figure 11. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

3.6.4 12-bit DAC electrical characteristics

3.6.4.1 12-bit DAC operating requirements

Table 33. 12-bit DAC operating requirements

Symbol	Desciption	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage		3.6	V	
V_{DACR}	Reference voltage	1.13	3.6	V	1
C_L	Output load capacitance	—	100	pF	2
I_L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or V_{REFH}.
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.

NOTE

The IRC48M do not meet the USB jitter specifications for certification for Host mode operation.

This device cannot support Host mode operation.

3.8.2 USB VREG electrical specifications

Table 35. USB VREG electrical specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
VREGIN	Input supply voltage	2.7	—	5.5	V	
I_{DDon}	Quiescent current — Run mode, load current equal zero, input supply (VREGIN) > 3.6 V	—	125	186	µA	
I_{DDstby}	Quiescent current — Standby mode, load current equal zero	—	1.1	10	µA	
I_{DDoff}	Quiescent current — Shutdown mode • VREGIN = 5.0 V and temperature=25 °C • Across operating voltage and temperature	— —	650 —	— 4	nA µA	
$I_{LOADrun}$	Maximum load current — Run mode	—	—	120	mA	
$I_{LOADstby}$	Maximum load current — Standby mode	—	—	1	mA	
$V_{Reg33out}$	Regulator output voltage — Input supply (VREGIN) > 3.6 V • Run mode • Standby mode	 3 2.1	 3.3 2.8	 3.6 3.6	 V V	
$V_{Reg33out}$	Regulator output voltage — Input supply (VREGIN) < 3.6 V, pass-through mode	2.1	—	3.6	V	2
C_{OUT}	External output capacitor	1.76	2.2	8.16	µF	
ESR	External output capacitor equivalent series resistance	1	—	100	mΩ	
I_{LIM}	Short circuit current	—	290	—	mA	

1. Typical values assume VREGIN = 5.0 V, Temp = 25 °C unless otherwise stated.
2. Operating in pass-through mode: regulator output voltage equal to the input voltage minus a drop proportional to I_{Load}.

3.8.3 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's Reference Manual for information about the modified transfer formats used for communicating with slower peripheral devices.

All timing is shown with respect to 20% V_{DD} and 80% V_{DD} thresholds, unless noted, as well as input signal transitions of 3 ns and a 30 pF maximum load on all SPI pins.

Table 36. SPI master mode timing on slew rate disabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	t_{SPSCK}	SPSCK period	2 x t_{periph}	2048 x t_{periph}	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} - 30	1024 x t_{periph}	ns	—
6	t_{SU}	Data setup time (inputs)	18	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_{v}	Data valid (after SPSCK edge)	—	15	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	t_{periph} - 25	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
2. $t_{periph} = 1/f_{periph}$

Table 37. SPI master mode timing on slew rate enabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	t_{SPSCK}	SPSCK period	2 x t_{periph}	2048 x t_{periph}	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} - 30	1024 x t_{periph}	ns	—
6	t_{SU}	Data setup time (inputs)	96	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—

Table continues on the next page...

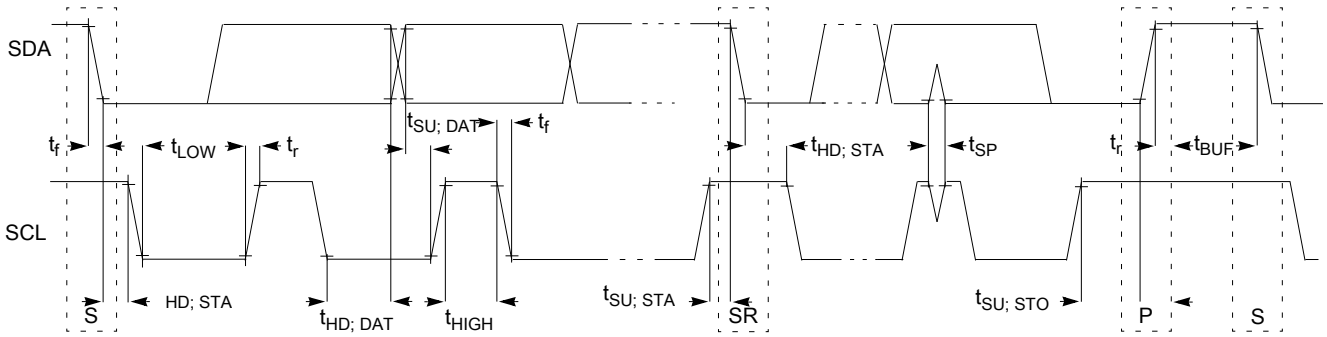


Figure 18. Timing definition for devices on the I²C bus

3.8.5 UART

See General switching specifications.

3.8.6 I2S/SAI switching specifications

This section provides the AC timing for the I2S/SAI module in master mode (clocks are driven) and slave mode (clocks are input). All timing is given for noninverted serial clock polarity (TCR2[BCP] is 0, RCR2[BCP] is 0) and a noninverted frame sync (TCR4[FSP] is 0, RCR4[FSP] is 0). If the polarity of the clock and/or the frame sync have been inverted, all the timing remains valid by inverting the bit clock signal (BCLK) and/or the frame sync (FS) signal shown in the following figures.

3.8.6.1 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

Table 42. I2S/SAI master mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK (as an input) pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15.5	ns

Table continues on the next page...

Table 42. I2S/SAI master mode timing (continued)

Num.	Characteristic	Min.	Max.	Unit
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	19	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	26	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

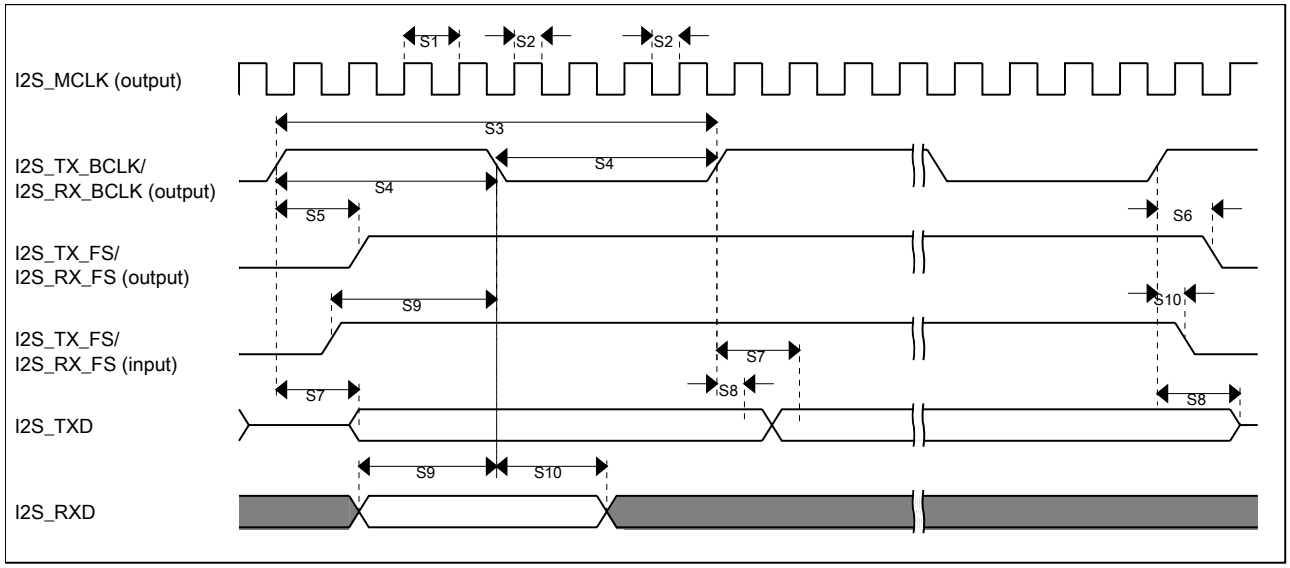


Figure 19. I2S/SAI timing — master modes

Table 43. I2S/SAI slave mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	80	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	10	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	33	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	10	—	ns

Table continues on the next page...

Table 44. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes (full voltage range) (continued)

Num.	Characteristic	Min.	Max.	Unit
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK		—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

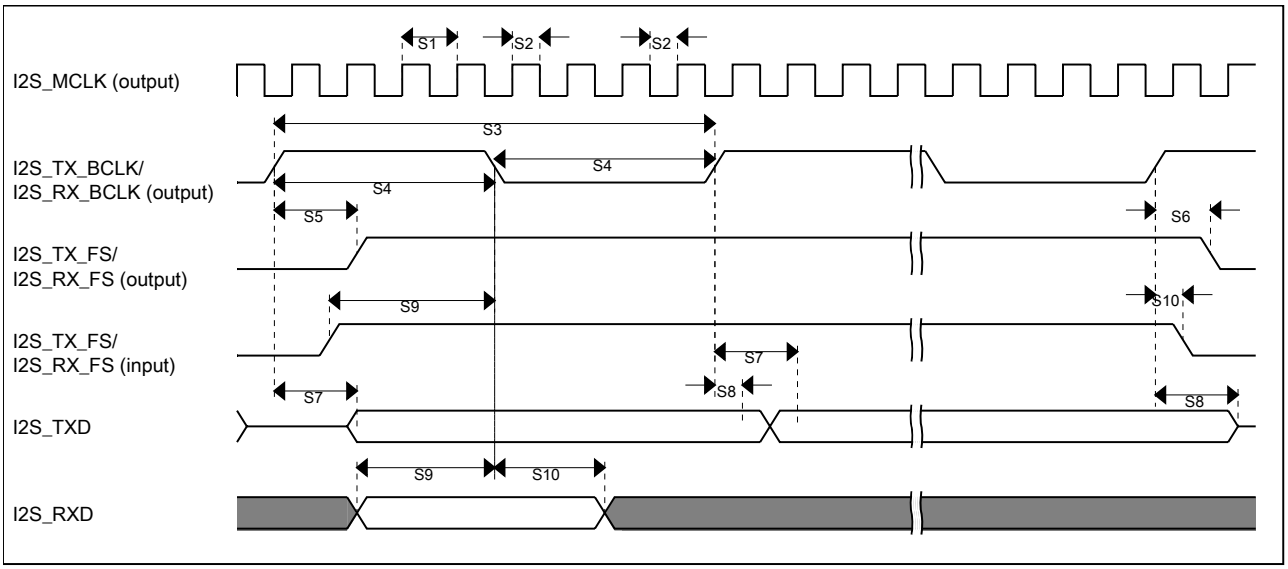


Figure 21. I2S/SAI timing — master modes

Table 45. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	250	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	87	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	72	ns

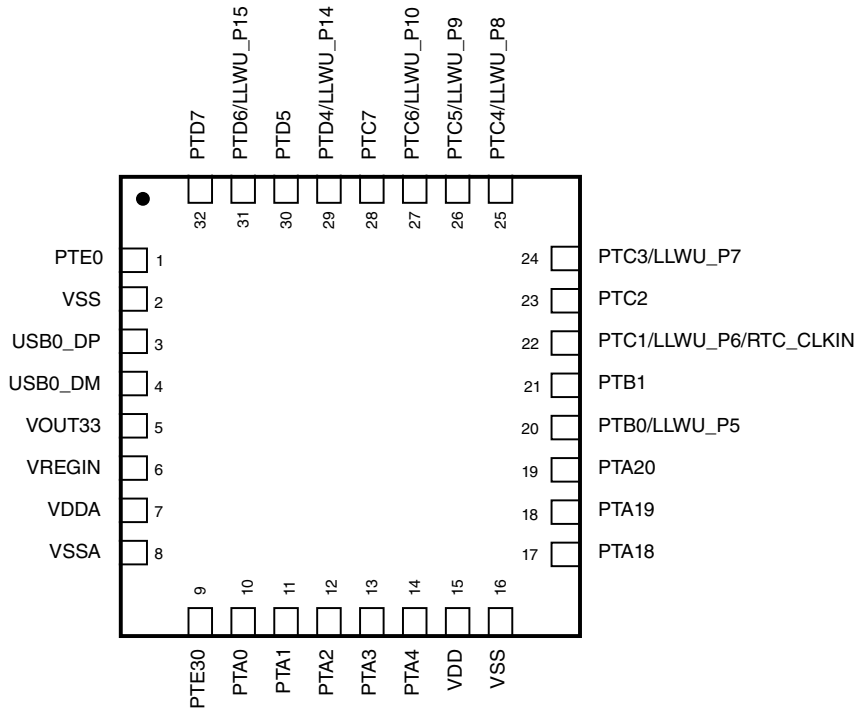


Figure 23. 32 QFN Pinout diagram

Figure below shows the 48 QFN pinouts:

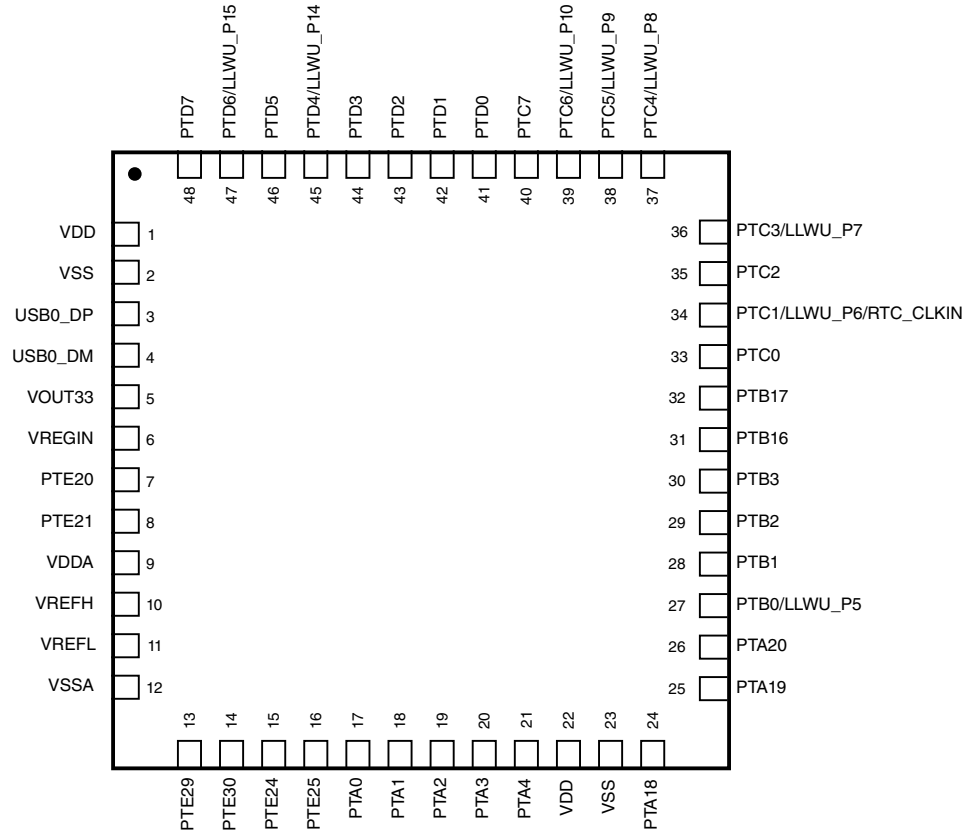


Figure 24. 48 QFN Pinout diagram

Figure below shows the 64 LQFP pinouts:

Table 47. Revision History (continued)

Rev. No.	Date	Substantial Changes

		• Updated Related Resources table to include Chip Errata resource name and Package Drawing part numbers in the respective rows. Also updated Product Brief resource references.
		• Updated Table 7. Voltage and current operating behaviors.
		  • Specified correct max. value for I_{IN}.
		• Updated Table - 9 Power consumption operating behaviors.
		  • Rows added for IDD for reset pin hold low ($I_{DD\_RESET\_LOW}$) at 1.7V and 3V.
		  • Measurement unit updated for I_{DD_VLLS1} from nA to µA.
		  • Footnote 1 was moved in the beginning of the table as text.
		• Added Table - 11 EMC radiated emissions operating behaviors for 64-pin LQFP package under section 2.2.6.
		• Updated Table - 18 (IRC48M specification) and Table - 19 (IRC8M/2M specification) under section 3.3.1 - 'MCG-Lite specifications'.
		  • Removed supply voltage (V_{DD}), temperature range (T), untrimmed (f_{IRC_UT}), trim function (Δf_{IRC_C}, Δf_{IRC_F}) data from Table - 18 (IRC48M specification).
		  • Removed supply voltage (V_{DD}), temperature range (T) data from Table - 19 (IRC8M/2M specification).
		• Added Figure 6. IRC8M Frequency Drift vs Temperature curve after Table - 19 (IRC8M/2M specification).
		• Updated Table 29. VREF full-range operating behaviors.
		  • Removed A_c(Aging coefficient) row.
		  • Added $T_{chop\_osc\_stup}$ parameter.
		• Added tables: "I2C timing" and "I2C 1Mbit/s timing" under section - I^2C.
		• Added VREF specifications (V_{REFH} and V_{REFL}) to Table 26. 16-bit ADC operating conditions.
		• Removed note: “This device does not have the USB_CLKIN signal available.”

5	12 August 2015	• In Table 9. Power consumption operating behaviors:
		  • Updated Max. values of I_{DD_WAIT}, I_{DD_VLPW}, I_{DD_STOP}, I_{DD_VLPS}, I_{DD_LLS}, I_{DD_VLLS3}, I_{DD_VLLS1}, I_{DD_VLLS0}.
		  • Modified unit of I_{DD_VLLS0} from nA to µA.
		  • Removed $I_{DD\_RESET\_LOW}$ information.
		• In Table 13. Device clock specifications, added a footnote for normal run mode.
		• In Table 15. Thermal operating requirements, modified the footnote for Ambient temperature.
		• In Table 18. IRC48M specification, removed f_{IRC_T} data and added $\Delta f_{irc48m\_of\_lv}$ and $\Delta f_{irc48m\_of\_hv}$ specifications.
		• In Table 26. 16-bit ADC operating conditions, updated Max. value of f_{ADCK} and C_{rate}.